Data Sheet | August 1, 2008 | FN3402.4

Radiation Hardened Quad Differential Line Receiver

The Intersil HS-26C32RH is a differential line receiver designed for digital data transmission over balanced lines and meets the requirements of EIA Standard RS-422. Radiation hardened CMOS processing assures low power consumption, high speed, and reliable operation in the most severe radiation environments.

The HS-26C32RH has an input sensitivity typically of 200mV over the common mode input voltage range of ±7V. The receivers are also equipped with input fail safe circuitry, which causes the outputs to go to a logic “1” when the inputs are open. Enable and Disable functions are common to all four receivers.

Specifications for Rad Hard QML devices are controlled by the Defense Supply Center in Columbus (DSCC). The SMD numbers listed in the “Ordering Information” table must be used when ordering.

Detailed Electrical Specifications for these devices are contained in SMD 5962-95689. A “hot-link” is provided on our homepage for downloading .**www.intersil.com/military/**

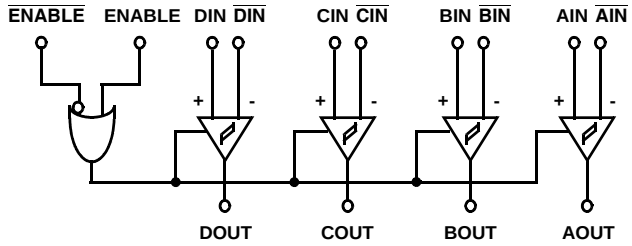
Features

- Electrically Screened to SMD # 5962-95689
- QML Qualified per MIL-PRF-38535 Requirements
- 1.2 Micron Radiation Hardened CMOS
  - Total Dose. . . . . 300 krad(Si) (Max)
- Latch-up Free
- EIA RS-422 Compatible Inputs
- CMOS Compatible Outputs
- Input Fail Safe Circuitry
- High Impedance Inputs when Disabled or Powered Down
- Low Power Dissipation 138mW Standby (Max)
- Single 5V Supply
- Full -55°C to +125°C Military Temperature Range

Applications

- Line Receiver for MIL-STD-1553 Serial Data Bus

Logic Diagram

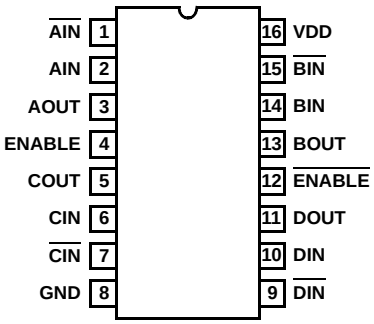


Ordering Information

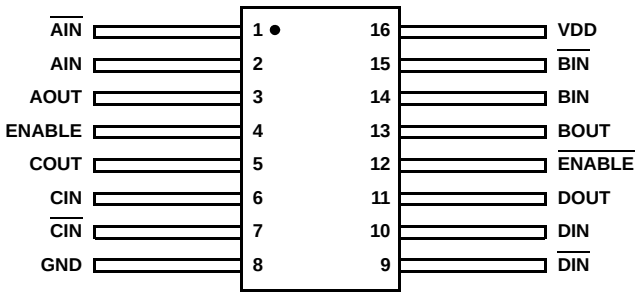
ORDERING NUMBER	INTERNAL MKT. NUMBER	PART MARKING	TEMP. RANGE (°C)	PACKAGE	PKG. DWG. #
5962F9568901QEC	HS1-26C32RH-8	Q 5962F95 68901QEC	-55 to +125	16 Ld SBDIP	D16.3
5962F9568901QXC	HS9-26C32RH-8	Q 5962F95 68901QXC	-55 to +125	16 Ld FLATPACK	K16.A
5962F9568901V9A	HS0-26C32RH-Q		-55 to +125		
5962F9568901VEC	HS1-26C32RH-Q	Q 5962F95 68901VEC	-55 to +125	16 Ld SBDIP	D16.3
5962F9568901VXC	HS9-26C32RH-Q	Q 5962F95 68901VXC	-55 to +125	16 Ld FLATPACK	K16.A
HS1-26C32RH/PROTO	HS1-26C32RH/PROTO	HS1- 26C32RH /PROTO	-55 to +125	16 Ld SBDIP	D16.3
HS9-26C32RH/PROTO	HS9-26C32RH/PROTO	HS9- 26C32RH /PROTO	-55 to +125	16 Ld FLATPACK	K16.A

Pinouts

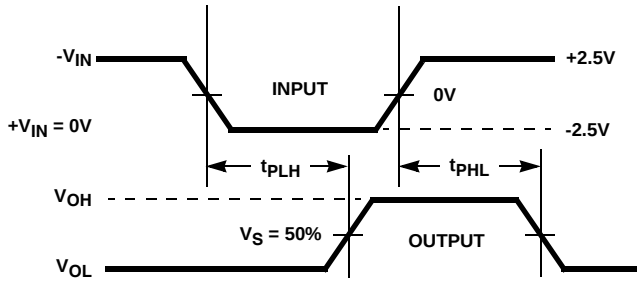
HS1-26C32RH
(16 LD SBDIP)
MIL-STD-1835: CDIP2-T16
TOP VIEW



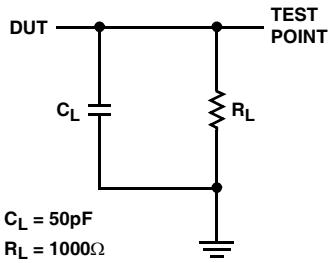
HS9-26C32RH
(16 LD FLATPACK)
MIL-STD-1835: CDFP4-F16
TOP VIEW



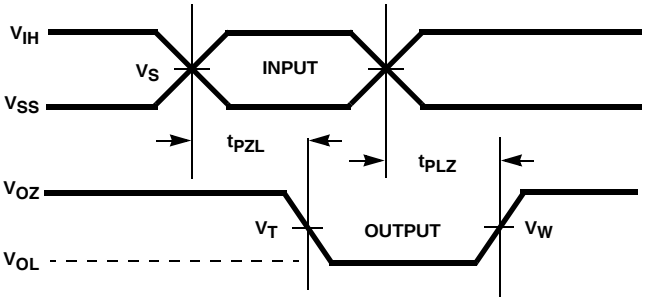
Propagation Delay Timing Diagram



Propagation Delay Load Circuit



Three-State Low Timing Diagram



Three-State High Timing Diagrams

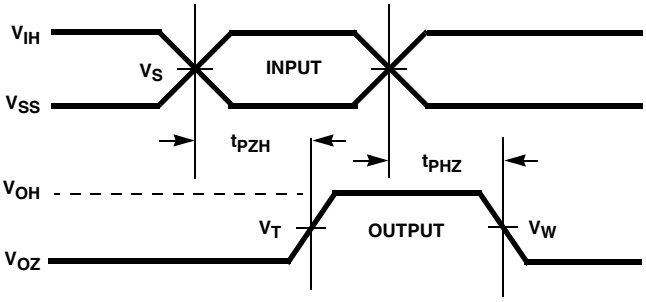


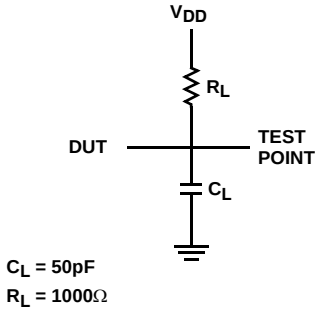
TABLE 1. THREE-STATE LOW VOLTAGE LEVELS

PARAMETER	HS-26C32RH	UNITS
V_{DD}	4.50	V
V_{IH}	4.50	V
V_S	2.25	V
V_T	50	%
V_W	V_{OL} + 0.5	V
GND	0	V

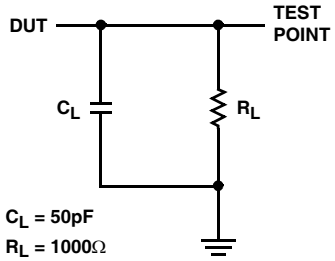
TABLE 2. THREE-STATE HIGH VOLTAGE LEVELS

PARAMETER	HS-26C32RH	UNITS
V_{DD}	4.50	V
V_{IH}	4.50	V
V_S	2.25	V
V_T	50	%
V_W	V_{OH} - 0.5	V
GND	0	V

Three-State Low Load Circuit



Three-State High Load Circuit



Die Characteristics

DIE DIMENSIONS:

84 mils x 130 mils
(2140µm x 3290µm)

INTERFACE MATERIALS:

Glassivation:

Type: SiO_2
Thickness: 10kÅ ± 1kÅ

Top Metallization:

M1: Mo/Tiw
Thickness: 5800Å
M2: Al/Si/Cu
Thickness: 5800Å

Worst Case Current Density:

$<2.0 \times 10^5 A/cm^2$

Bond Pad Size:

110µm x 100µm

Metallization Mask Layout

HS-26C32RH